

AMENDMENTS TO THE SPECIFICATION

Please delete the present Abstract of the Disclosure.

Please add the following new Abstract of the Disclosure:

A nitride semiconductor product including an n-type layer, a light-emitting layer, and a p-type layer which are formed of a nitride semiconductor and sequentially stacked on a substrate in the above order, the light-emitting layer having a quantum well structure in which a well layer is sandwiched by barrier layers having band gaps wider than the band gap of the well layer. Each barrier layer includes a barrier sublayer C which has been grown at a temperature higher than a growth temperature of the well layer, and a barrier sublayer E which has been grown at a temperature lower than a growth temperature of the barrier sublayer C. The barrier sublayer C is disposed closer to the substrate with respect to the barrier sublayer E.